

IN THE SPECIFICATION:

Paragraph beginning at page 6, line 35 has been amended as follows:

The present invention solves the above problems by providing a thin-film circuit substrate and a manufacturing method thereof, as follows. The thin-film circuit substrate includes a semiconductor substrate that has a first principal plane and a second principal plane that counters the first principal plane, a first insulation film formed on the first principal plane, and through holes that extend continuously from the second principal plane to the first principal plane, completely through the semiconductor substrate, the through holes including a main section starting from the second principal plane and a tapered section formed near the first principal plane. The manufacturing method includes a step of forming an etching stop film on the first principal plane of the semiconductor substrate that is formed by the first and the second principal planes, a step of forming a resist pattern which has resist openings on the second principal plane of the semiconductor substrate, a step of dry etching the semiconductor substrate using the resist pattern as a mask such that through holes are provided corresponding to the resist openings to the semiconductor substrate and such that the etching stop film is exposed at the through holes, a step of forming an insulator film ~~on the~~ on the side wall face of the through holes, and a step of removing the etching stop film at the through holes such that openings are formed, exposing the thin-film circuit.

Paragraph beginning at page 21, line 7 has been amended as follows:

The present application is based on Japanese priority application No. ~~2001-262329~~ 2001-262359 filed on August 30, 2001, with the Japanese Patent Office, the entire contents of which are hereby incorporated by reference.